

Figure 1: Saturation curves displaying controlled growth of HfO₂. The films were grown at a table temperature of 350 °C. The encircled values were used for the other saturation curves

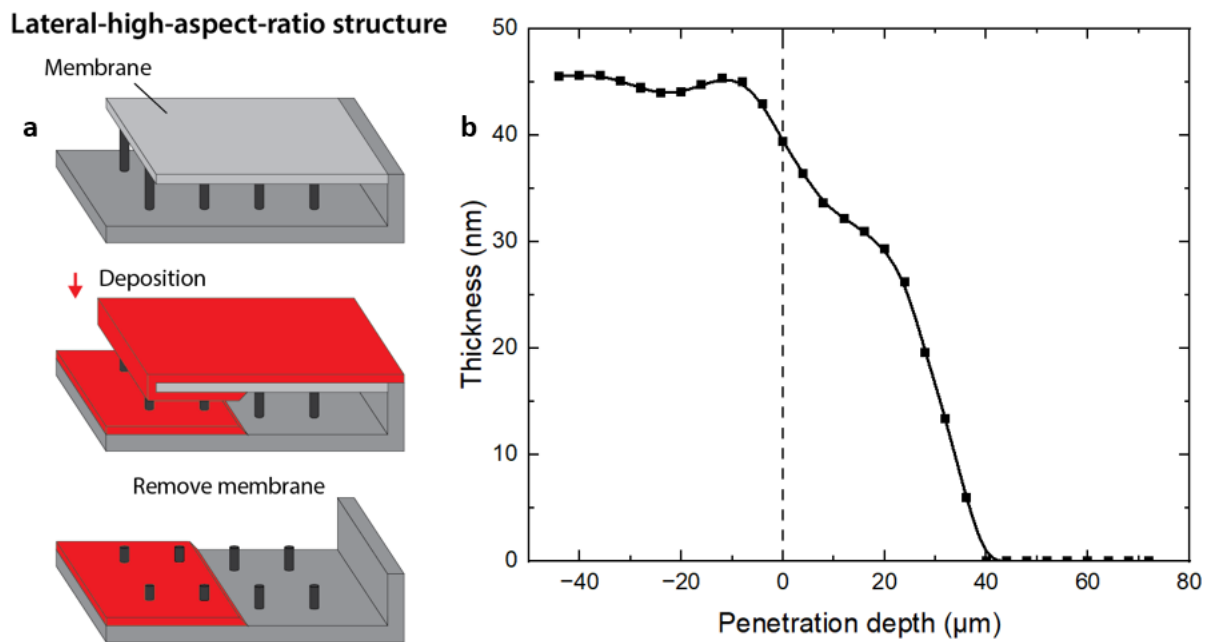


Figure 2: a) Schematic representation of the lateral high-aspect ratio PillarHall™ chip. A film is deposited by ALD on the top surface and into the trench. After deposition, the top membrane is peeled off, such that the film within the trench can be measured from the top by reflectometry, spectroscopic ellipsometry (SE), and x-ray photoelectron spectroscopy (XPS). b) Thickness profile of HfO₂ as obtained from reflectometry.